

ABSTRACT OF THE DISCLOSURE

The method of manufacturing the semiconductor device includes the steps of forming terminal portions convexly protruding on a surface of first conductive foil by etching the first conductive foil except portions to become terminals, superimposing a resin sheet on the first conductive foil such that the terminal portions are embedded in the resin sheet, constructing a laminated sheet by superimposing second conductive foil having a resin layer formed on a back thereof, on the resin sheet with the resin layer faced down, forming a conductive pattern by etching the second conductive foil, electrically connecting the conductive pattern and the terminal portions, electrically isolating the terminal portions from each other, firmly fixing a semiconductor element to the laminated sheet and electrically connecting the semiconductor element and the conductive pattern, and forming sealing resin on a surface of the laminated sheet such that the semiconductor element is covered by the sealing resin.